

**60 A, 400 V - 600 V,
Hyperfast Dual Diode**

Description

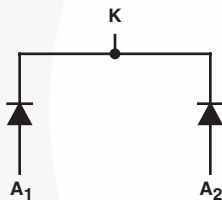
The RHRG3040CC, RHRG3060CC is a hyperfast dual diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRG3040CC	TO-247	RHRG3040C
RHRG3060CC	TO-247	RHRG3060C

NOTE: When ordering, use the entire part number.

Symbol



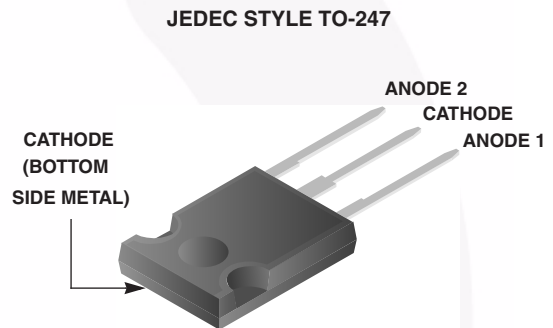
Features

- Hyperfast Recovery $t_{rr} = 45 \text{ ns}$ (@ $I_F = 30 \text{ A}$)
- Max Forward Voltage, $V_F = 2.1 \text{ V}$ (@ $T_C = 25^\circ\text{C}$)
- High Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging



Absolute Maximum Rating (Per Leg) $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RHRG3040CC	RHRG3060CC	UNIT	
Peak Repetitive Reverse Voltage	V_{RRM}	400	600	V
Working Peak Reverse Voltage	V_{RWM}	400	600	V
DC Blocking Voltage	V_R	400	600	V
Average Rectified Forward Current ($T_C = 120^\circ\text{C}$)	$I_{F(AV)}$	30	30	A
Repetitive Peak Surge Current (Square Wave, 20 kHz)	I_{FRM}	70	70	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60 Hz)	I_{FSM}	325	325	A
Maximum Power Dissipation	P_D	125	125	W
Avalanche Energy (See Figures 10 and 11)	E_{AVL}	20	20	mJ
Operating and Storage Temperature	T_{STG}, T_J	-65 to 175	-65 to 175	$^\circ\text{C}$

RHRG3040CC, RHRG3060CC

Electrical Specification (Per Leg) $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRG3040CC			RHRG3060CC			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V_F	$I_F = 30\text{ A}$	-	-	2.1	-	-	2.1	V
	$I_F = 30\text{ A}, T_C = 150^\circ\text{C}$	-	-	1.7	-	-	1.7	V
I_R	$V_R = 400\text{ V}$	-	-	250	-	-	-	μA
	$V_R = 600\text{ V}$	-	-	-	-	-	250	μA
	$V_R = 400\text{ V}, T_C = 150^\circ\text{C}$	-	-	1.0	-	-	-	mA
	$V_R = 600\text{ V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	1.0	mA
t_{rr}	$I_F = 1\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	-	-	40	-	-	40	ns
	$I_F = 30\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	-	-	45	-	-	45	ns
t_a	$I_F = 30\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	-	22	-	-	22	-	ns
t_b	$I_F = 30\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	-	18	-	-	18	-	ns
Q_{rr}	$I_F = 30\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}$	-	100	-	-	100	-	nC
C_J	$V_R = 10\text{ V}, I_F = 0\text{ A}$	-	85	-	-	85	-	pF
$R_{\theta JC}$		-	-	1.2	-	-	1.2	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

T_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{rr} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

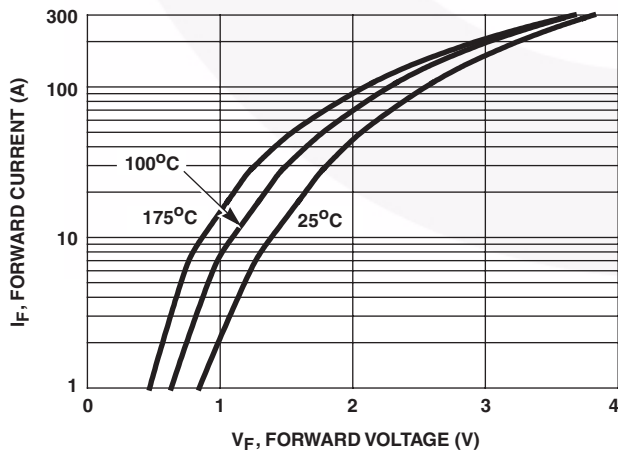


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

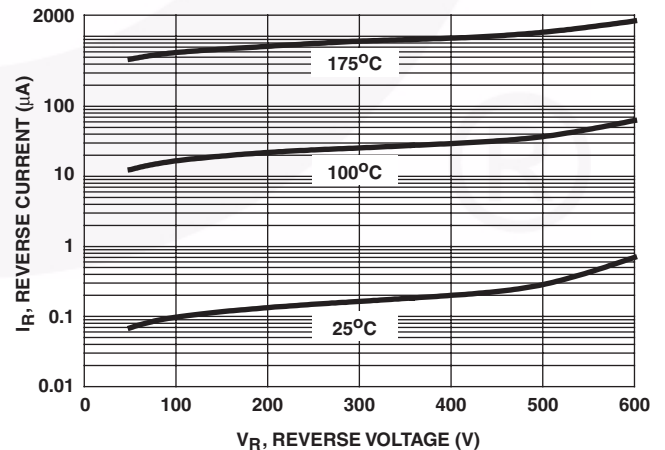


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

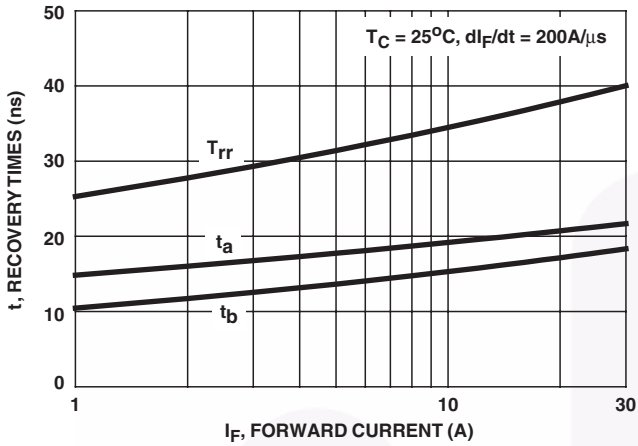


FIGURE 3. T_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

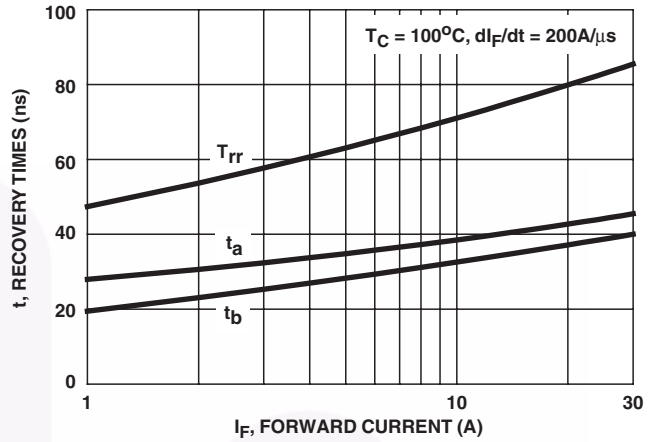


FIGURE 4. T_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

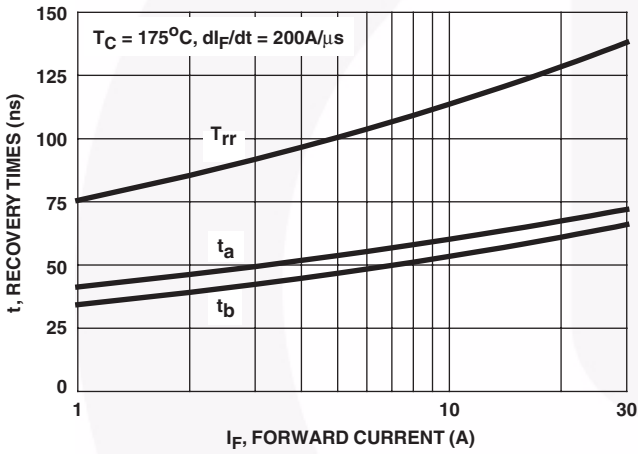


FIGURE 5. T_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

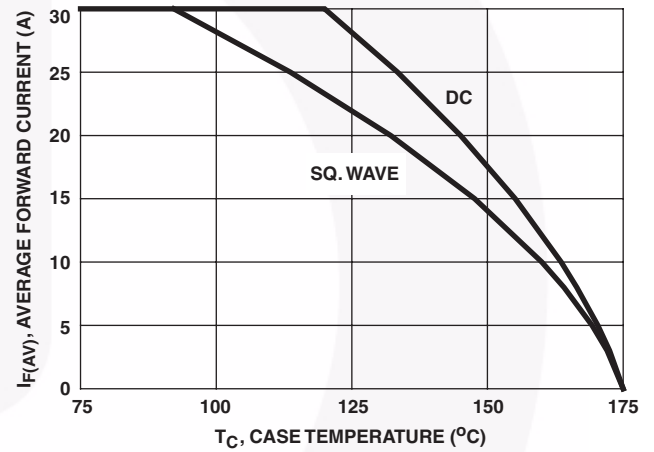


FIGURE 6. CURRENT DERATING CURVE

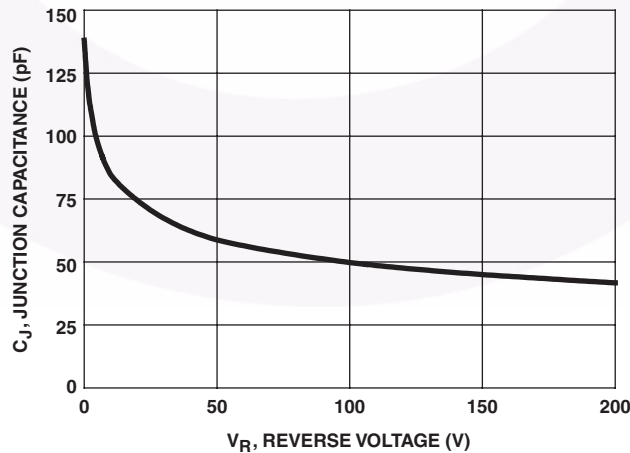


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuits and Waveforms

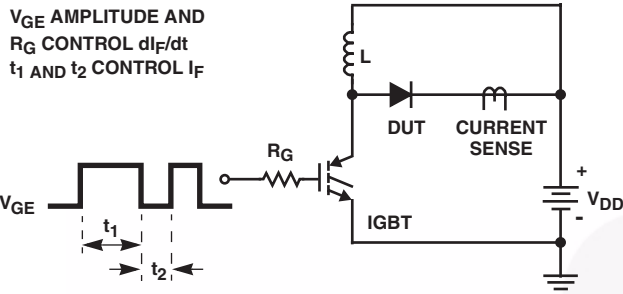
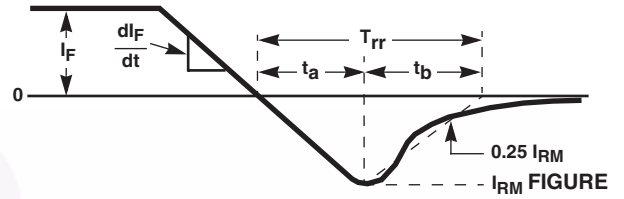


FIGURE 8. T_{rr} TEST CIRCUIT



9. T_{rr} WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

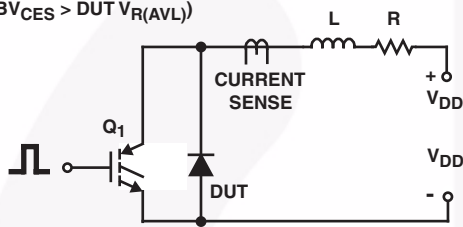


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

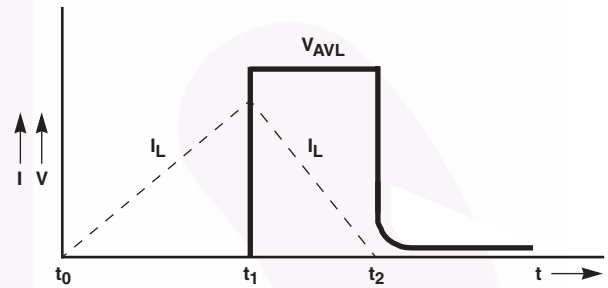
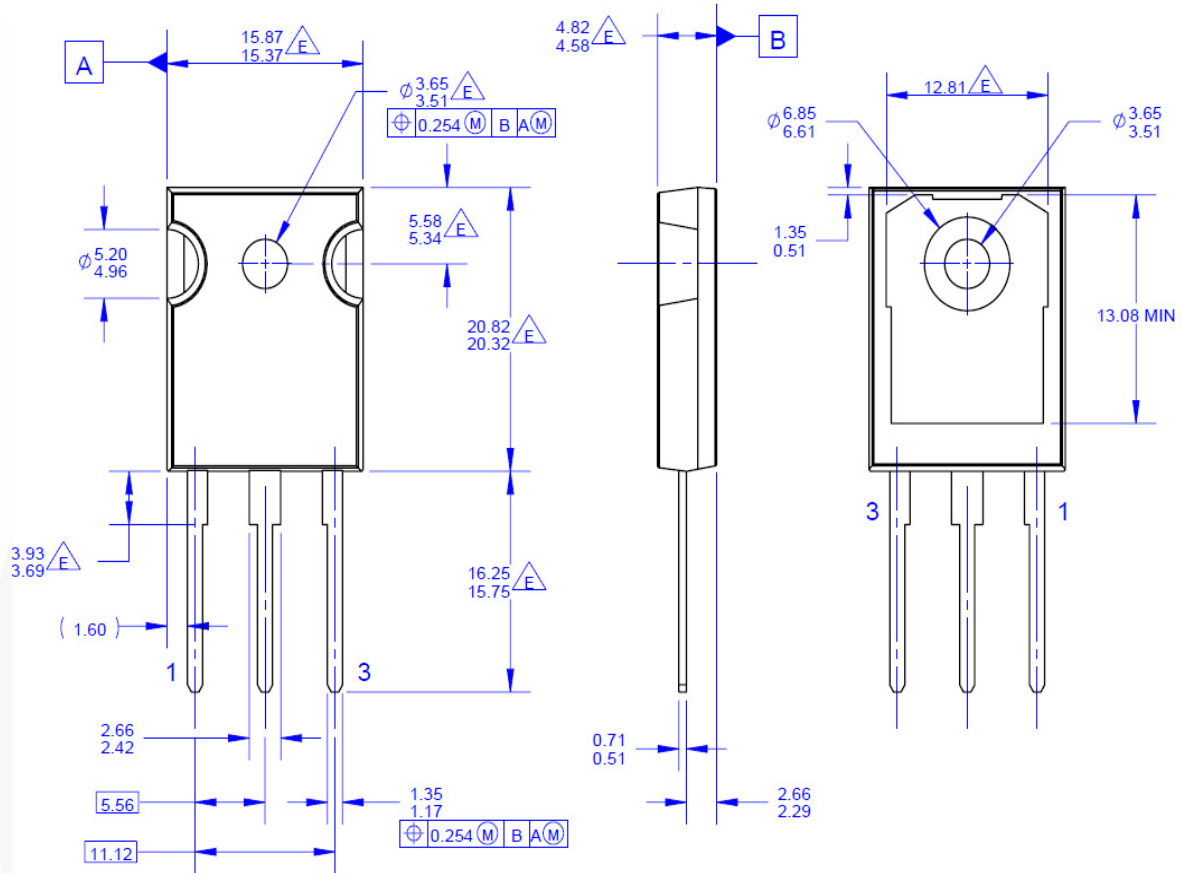


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

TO247-3L



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- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

- $\triangle E$ DOES NOT COMPLY JEDEC STANDARD VALUE
- F. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 12. TO-247, Molded, 3LD, Jedec Option AB

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